1. Scope

The present specifications shall apply to an FMX-G26S.

2. Outline

Type	Silicon Diode
Structure	Resin Molded
Applications	High Frequency Rectification

3. Flammability

UL94V-0(Equivalent)

4. Absolute maximum ratings

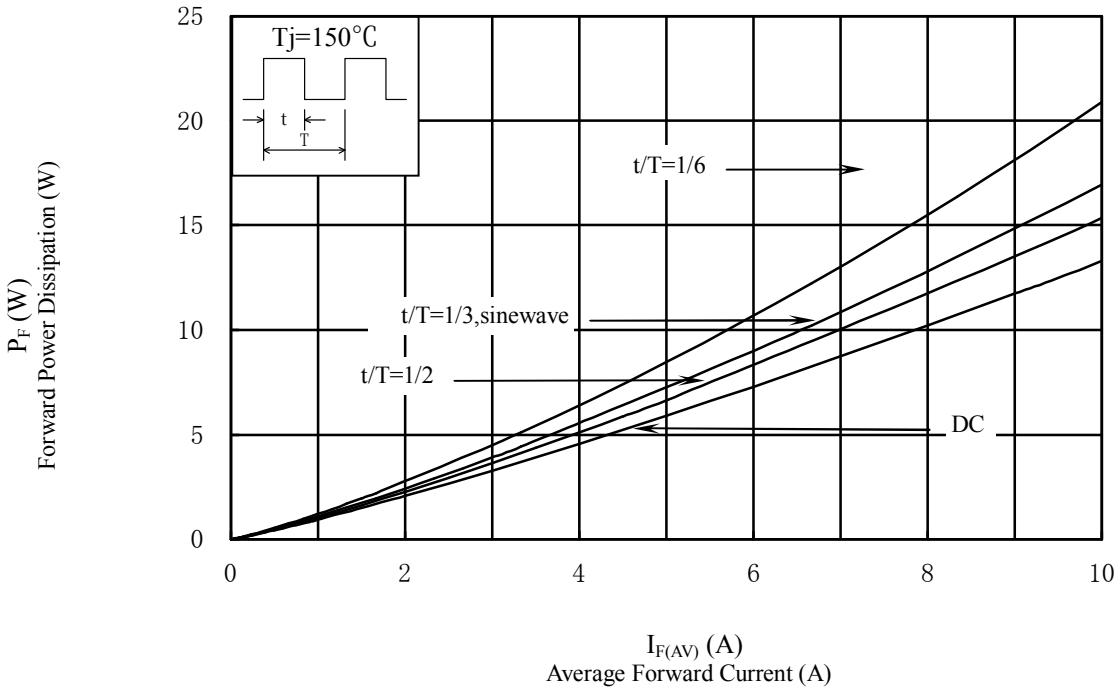
No.	Item	Symbol	Unit	Rating	Conditions
1	Transient Peak Reverse Voltage	V_{RSM}	V	600	
2	Peak Reverse Voltage	V_{RM}	V	600	
3	Average Forward Current	$I_{F(AV)}$	A	10	Refer to Derating of 7
4	Peak Surge Forward Current	I_{FSM}	A	100	10msec. Half sinewave, one shot
5	I^2t Limiting Value	I^2t	A^2s	50	1msec≤t≤10msec
6	Junction Temperature	T_j	°C	-40~+150	
7	Storage Temperature	T_{stg}	°C	-40~+150	

5. Electrical characteristics (Ta=25°C , unless otherwise specified)

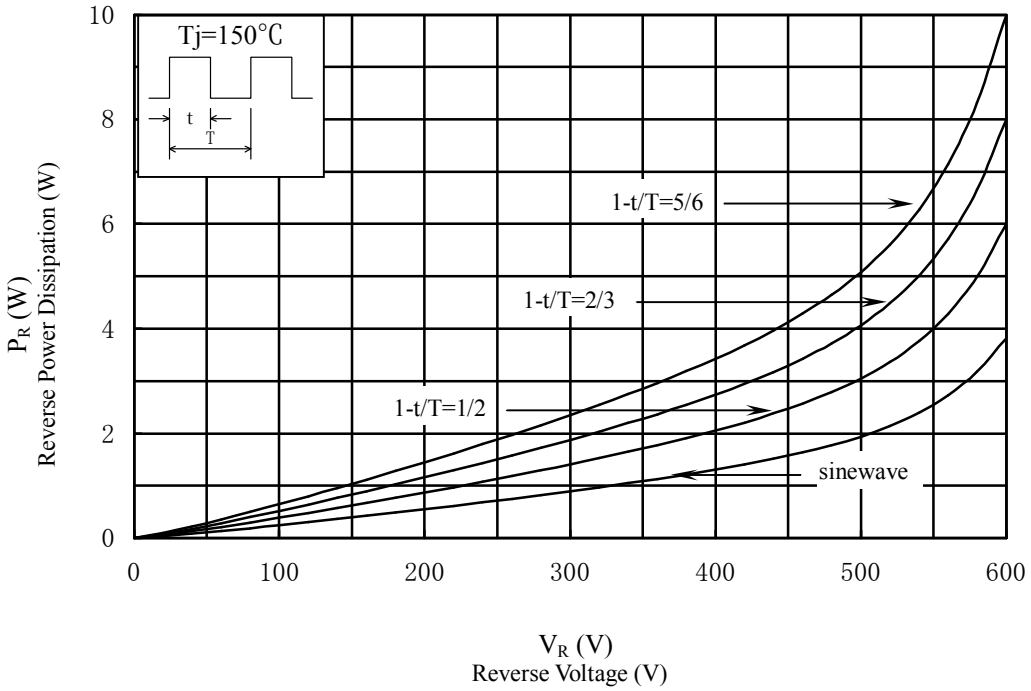
No.	Item	Symbol	Unit	Value	Conditions
1	Forward Voltage Drop	V_F	V	1.5 max.	I_F=10A
2	Reverse Leakage Current	I_R	uA	100 max.	$V_R=V_{RM}$
3	Reverse Leakage Current Under High Temperature	$H \cdot I_R$	mA	20 max.	$V_R=V_{RM}$, T_j=150°C
4	Reverse Recovery Time	trr1	ns	30 max.	$I_F=I_{RP}$=500mA 90% Recovery point, T_j=25°C
		trr2	ns	25 max.	I_F=500mA,I_{RP}=1A 75% Recovery point ,T_j=25°C
5	Thermal Resistance	$R_{th(j-c)}$	°C /W	4.0 max.	Between Junction and case

6. Characteristics

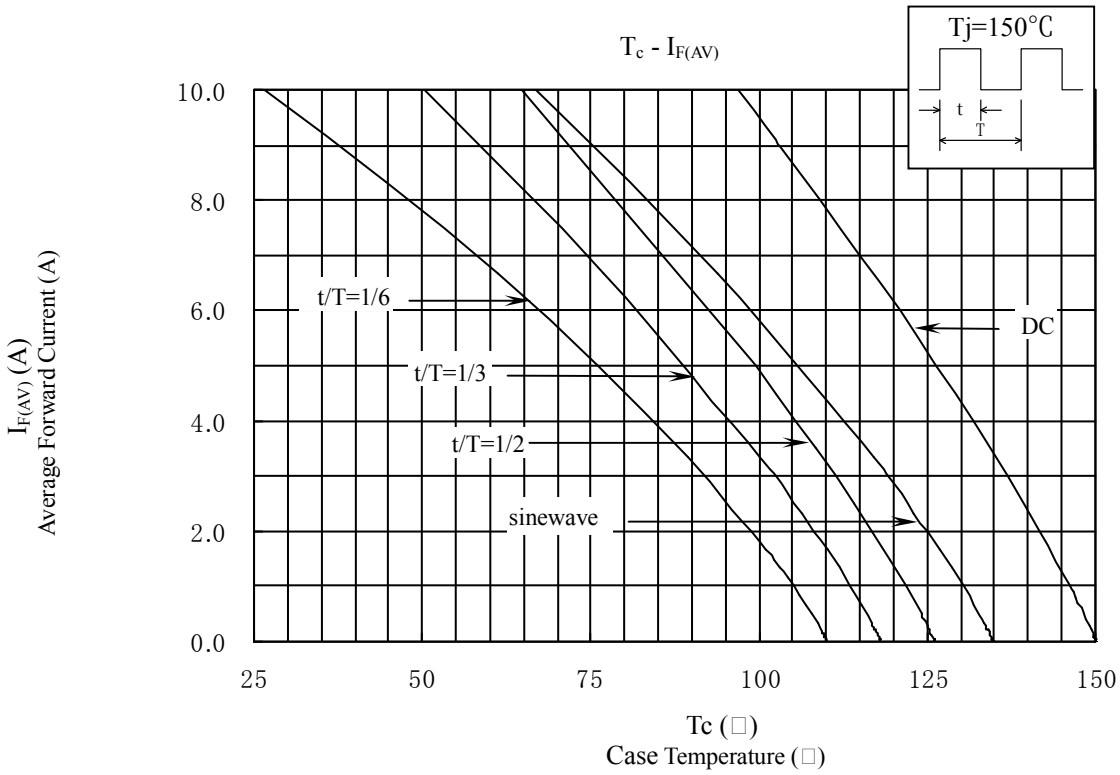
$I_{F(AV)}$ - P_F



V_R - P_R

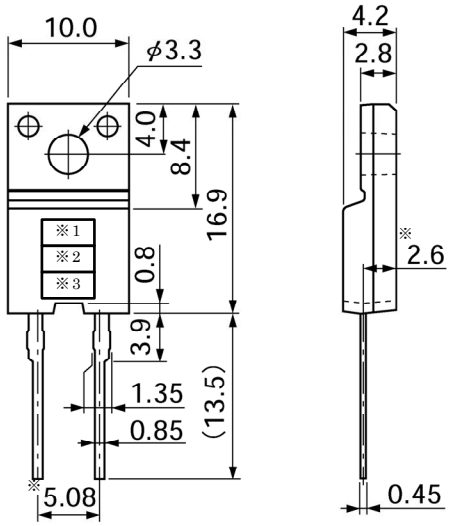


7. Derating


Tc - IF(AV)
Tj=150°C
t
T
10.0
8.0
6.0
4.0
2.0
0.0
t/T=1/6
t/T=1/3
t/T=1/2
sinewave
DC
25
50
75
100
125
150
IF(AV) (A)
Average Forward Current (A)
Tc (□)
Case Temperature (□)

8. Package information

8-1Package type, physical dimensions and material



*：root dimension

tolerance ±0.2

Dimensions in mm

8-2Appearance

The body shall be clean and shall not bear any stain, rust or flaw.

8-3Marking

Type Name	Marking		
	*1 Type Name	*2 Polarity	*3 Lot number
FMX-G26S	FMXG26	S	1st letter: Last digit of year 2nd letter: Month From 1 to 9 for Jan. to Sep., O for Oct., N for Nov., D for Dec. 3rd & 4th letter: Day ex. 5208 (Feb.8, 2005)